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Synthesis, Crystal Structure, Magnetism, and Optical Properties of $\text{Gd}_3[\text{SiON}_3]\text{O}$ —An Oxonitridosilicate Oxide with Noncondensed SiON_3 Tetrahedra

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DEDICATED TO GALEN D. STUCKY ON THE OCCASION OF HIS 65TH BIRTHDAY

INTRODUCTION

Nitridosilicates are derived from the classical oxosilicates (which are made up of SiO_4 tetrahedra) by a formal exchange of oxygen by nitrogen. Thus, they contain SiN_4 tetrahedra. This substitution results in a significant extension of the structural possibilities (1, 2). Oxonitridosilicates (so-called “sions”) represent an intermediate class of compounds between oxosilicates and nitridosilicates. During the last few years, we developed a synthetic route towards sions and sialons using SrCO_3 as an appropriate oxygen source (3). In this paper, we report on the synthesis of a new sion using gadolinium carbonate instead of SrCO_3 .

The crystal structure of the recently synthesized oxonitridosilicate oxide $\text{Ce}_4[\text{Si}_4\text{O}_4\text{N}_6]\text{O}$ consists of complex $[\text{Ce}_4\text{O}]^{10+}$ cations encased by a hyperbolic layer $[\text{Si}_4\text{O}_4\text{N}_6]^{10-}$ (4). Compounds containing oxygen centered tetrahedral $[\text{OM}_4]^{n+}$ cations have been found frequently (5). Structures containing oxygen-centered octahedra are also well known. For example $[\text{OM}_6]^{4+}$ ($M = \text{K}, \text{Cs}, \text{Rb}$) in $M_3\text{AuO}$ (6), $[\text{OCa}_6]^{10+}$ in $\text{Ca}_5[\text{WN}_4]\text{O}_2$ (7), $[\text{OBa}_6]^{10+}$ in $\text{Ba}_3[\text{SiO}_4]\text{O}$ (8, 9), $\text{Ba}_{11}\text{KX}_7\text{O}_2$ ($X = \text{P}, \text{As}$) (10), $\text{Ba}_3\text{In}_2\text{Zn}_5\text{O}_{11}$ (11), $\text{Ba}_6\text{Lu}_4\text{Zn}_{10}\text{O}_{22}$ (12), and in inverse perovskite-type Ba_3XO ($X = \text{Ge}, \text{Si}$) (13). $[\text{OV}_6]$ octahedra which are stabilized by $\mu^4\text{-Te}^{2-}$ and $\mu^3\text{-Se}^{2-}$ are found in $\text{KV}_3\text{Te}_3\text{O}_{0.42}$ (14) and $\text{V}_6\text{Se}_8\text{O}(\text{PMe}_3)_6$ (15), respectively.

The herein described new sion $\text{Gd}_3[\text{SiON}_3]\text{O}$ contains distorted oxygen-centered octahedra $[\text{OGd}_6]$ which carry a high formal charge $16+$ if viewed as an isolated complex cation.

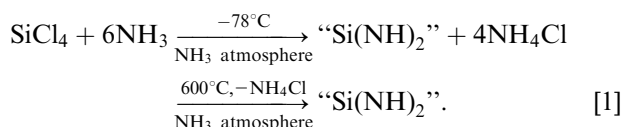
EXPERIMENTAL PROCEDURE

Synthesis of Silicon Diimide “ $\text{Si}(\text{NH})_2$ ”

Using “ $\text{Si}(\text{NH})_2$ ” instead of the relatively unreactive Si_3N_4 as starting material proved to be advantageous for

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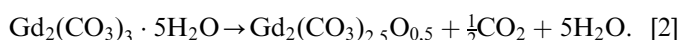
the synthesis of the nitridosilicates and this also holds for the sions and sialons (1–3). “Si(NH)₂” was obtained by ammonolysis of SiCl₄ in CH₂Cl₂ followed by a thermal treatment at 600°C under an atmosphere of pure NH₃:



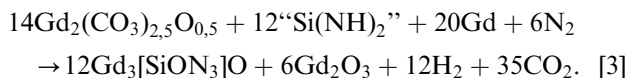
A detailed description of the synthesis of “Si(NH)₂” is given in Ref. (3). “Si(NH)₂” was yielded as an X-ray amorphous and relatively undefined but reactive product which is converted to amorphous Si₃N₄ at temperatures above 900°C. It is an important precursor for the technical production of Si₃N₄ ceramics (16).

Synthesis of Gd₃[SiON₃]O

Under nitrogen atmosphere, Gd₂(CO₃)₃·nH₂O (STREM chemicals, 99.99%) was dehydrated and partially decarbonated (17) at 500°C according to Eq. (2). A DTA analysis revealed a weight loss of 20.2% corresponding to *n* = 5 and approximately ½CO₂ in agreement with Ref. (17):



In an argon-filled glove box 244 mg (0.496 mmol) of this dehydrated product, 240.9 mg (1.532 mmol) Gd metal (average particle size ≈ 0.5 mm, chempur, 99.9%) and 58.1 mg silicon diimide were thoroughly mixed. The synthesis of Gd₃[SiON₃]O was performed in a radio-frequency (r.f.) furnace under a nitrogen atmosphere according to Eq. (3). The mixture was heated to 1000°C within 5 min and maintained at this temperature for 25 min before further heating to 1400°C within 12 h and maintained at this temperature for 8 h. Then the mixture was cooled down to 600°C within 5 h. Further details about the experimental setup are given in Refs. (3, 18). Gd₃[SiON₃]O was obtained as a coarsely crystalline yellowish main product besides colorless Gd₂O₃. The title compound could easily be separated from the by-product due to their differing crystal habit and color. Due to the low degree of condensation the product undergoes slow hydrolysis in humid air:



The results of the EDX analysis revealed a molar ratio of Gd:Si = 3:1. The elemental analysis (Pascher, Remagen, precision ≈ 0.5% (O, N), ≈ 0.5% (Si), ≈ 1.0% (Gd)) fairly agrees with the theoretical values (in brackets): Gd 80.3 wt% (82.2%), Si 4.8% (4.9%), O 5.8% (5.6%), N 9.1% (7.3%). There was no evidence of a phase width of the compound.

UV–Vis Measurements

For the measurement of UV–Vis absorption spectra in reflection geometry, a Hitachi U-3501 spectrophotometer was used. The spectra were recorded at room temperature between 300 and 700 nm. Below 300 nm, the background absorption of the object slide on which the samples were fixed grew rapidly.

Magnetic Measurements

Temperature-dependent magnetic susceptibility data of a polycrystalline, powdered sample of Gd₃[SiON₃]O were measured with an MPMS XL SQUID magnetometer (Quantum Design) from 2 to 300 K with magnetic flux densities up to 5 T. A quantity of 6.645 mg (identical sample as used for powder X-ray diffraction) was enclosed in a silica tube and fixed at the sample holder rod. The sample was then cooled to 2 K in zero magnetic field and slowly heated to room temperature in an applied external field.

Vibrational Spectroscopy

FTIR spectra were obtained at room temperature by using a Bruker IFS 66v/S spectrometer. The samples were thoroughly mixed with dried KBr (5 mg sample, 500 mg KBr). Raman spectra were excited by a Bruker FRA 106/S module with an Nd–YAG laser (λ = 1064 nm) scanning a range from 100 to 3500 cm⁻¹. All sample preparations have been performed in a glove box under dried argon atmosphere.

CRYSTAL STRUCTURE ANALYSIS AND LATTICE ENERGY CALCULATIONS

Crystal Structure Analysis at *T* = 293 K

X-ray diffraction data of the title compound Gd₃[SiON₃]O were collected on a Stoe Stadi4 four-circle diffractometer using MoKα radiation: The single crystal was enclosed in a silica tube (0.2 mm) sealed under argon atmosphere. The diffraction data were corrected for an intensity decay (+9%). According to the observed extinction conditions (all reflections *hkl* with *h* + *k* + *l* = 2*n*, *hk0* with *h* + *k* = 2*n*, *0kl* with *k*, *l* = 2*n*, *hhl* with *l* = 2*n*, and *00l* with *l* = 2*n*) the space groups *I4/mcm*, *I4cm*, and *I4c2* were taken into account. The structure solution and refinement was only possible using space group *I4/mcm* (no. 140).

The crystal structure of Gd₃[SiON₃]O was solved by direct methods using SHELXTL (19) and refined with anisotropic displacement parameters for all atoms. The relevant crystallographic data and further details of the X-ray data collection are summarized in Table 1. Table 2

TABLE 1
Crystallographic Data of Gd₃[SiON₃]O (e.s.d.'s. in Parentheses)
for the Refinement at 293 K

<i>Crystal Data</i>	
Gd ₃ [SiON ₃]O	$F(000) = 972$
$M = 573.87$ g/mol	$\rho = 8.355$ g/cm ³
Tetragonal	MoK α -radiation
Space group $I4/mcm$ (no. 140)	$\lambda = 71.073$ pm
$a = 650.4(2)$ pm	$\mu = 43.25$ mm ⁻¹
$c = 1079.2(7)$ pm	$T = 293(2)$ K
$V = 456.5(4) \times 10^6$ pm ³	Block
$Z = 4$	$0.083 \times 0.074 \times 0.069$ mm ³
	Yellow
<i>Data collection (293 K)</i>	
Stoe STADI4	Measured octants: all
Absorption correction: numerical (ψ -scans)	$h = -6 \rightarrow 6$
$T_{\min} = 0.0849$; $T_{\max} = 0.1287$	$k = -6 \rightarrow 6$
$R_{\text{int}} = 0.0672$	$l = -11 \rightarrow 11$
$2\theta_{\max} = 44.9^\circ$	93 independent reflections
	84 observed reflections
	$(F_o^2 \geq 2\sigma(F_o^2))$
<i>Refinement (293 K)</i>	
Refinement on F^2	Program used to refine structure: SHELXL-97 (19)
$R_1 = 0.0215$ (all data)	$w^{-1} = \sigma^2 F_o^2 + (xP)^2 + yP$; $P = (F_o^2 + 2F_c^2)/3$
$wR_2 = 0.0324$ (all data)	Weighting scheme (x/y) 0.0141/0
GooF = 1.211	Extinction coefficient: 0.0019(2)
2063 measured reflections	Min. residual electron density: -0.702 eÅ ⁻³
18 parameters	Max. residual electron density: 0.991 eÅ ⁻³
<i>Powder diffraction (Rietveld refinement of the lattice parameters)</i>	
Gd ₃ [SiON ₃]O	Program used to refine lattice parameters: GSAS (20)
MoK α -radiation	$wR_p = 0.0745$
$a = 650.66(2)$ pm	$R_p = 0.0578$
$c = 1079.99(3)$ pm	$R_{F_2} = 0.0762$
$V = 457.23(2) \times 10^6$ pm ³	$R_F = 0.0548$
	$\chi^2 = 0.8468$
	198 reflections ($2\theta_{\max} = 60.0^\circ$)

shows the positional and displacement parameters for all atoms. In Table 5, selected interatomic distances and angles are listed. Furthermore, all reflections detected by X-ray powder diffraction (Stoe Stadi P) of single-phase Gd₃[SiON₃]O have been indexed and their observed intensities are in good agreement with the calculated diffraction pattern based on the single-crystal data. The Rietveld refinement of the lattice parameters (Table 1) has been performed with the program GSAS (20). The powder diffraction pattern of Gd₃[SiON₃]O is shown in Fig. 1. The asterisk in Fig. 1 indicates the strongest reflection of the

by-product Gd₂O₃. A two-phase refinement yielded a content of this by-product of ca. 1%.

Due to their identical electronic configuration and their very similar atomic form factors, the unequivocal differentiation of N³⁻/O²⁻ by X-ray diffraction is not reliable. Therefore, the assignment of the Gd, Si, O and N atoms to their crystallographic positions in Gd₃[SiON₃]O was checked by lattice energy calculations using the MAPLE concept (MAPLE = Madelung Part of Lattice Energy) (21–23). To our experience, MAPLE calculations usually are an appropriate tool to analyze O/N distributions in oxonitrides, and in several cases we have been able to confirm these results by neutron diffraction (4, 24). The results of these calculations are summarized in Table 6. They are in very good agreement with the expected data.

Further details of the crystal structure investigations reported in this paper may be obtained from the Fachinformationszentrum Karlsruhe, D-76344 Eggenstein-Leopoldshafen, Germany, by quoting the depository number CSD-412373 (investigation at 293 K) and CSD-412374 (investigation at 123 K).

The crystal structure of Gd₃[SiON₃]O is isotypic with that of Ba₃[SiO₄]O (8, 9) and Cs₃[CoCl₄]Cl (25) and it derives from perovskite CaTiO₃ by hierarchical substitution: Ti⁴⁺ → O²⁻, O²⁻ → Gd³⁺, Ca²⁺ → [SiON₃]⁷⁻. The resulting OGd₆ octahedra are subsequently twisted by $\xi = 16.47(1)^\circ$ around [001]. In conclusion, the crystal structure of Gd₃[SiON₃]O consists of corner-sharing OGd₆ octahedra which are elongated along [001]. The resulting large vacancies are filled by non-condensed SiON₃ tetrahedra (Figs. 2 and 3).

The twisting of the above-mentioned elongated [OGd₆]¹⁶⁺ octahedra presumably is caused by electrostatic reasons or size effects. In perovskite, Ca²⁺ is surrounded by 12 O²⁻ ions. Contrarily in Gd₃[SiON₃]O the formal Si⁴⁺, although shielded in their SiON₃ tetrahedra, are surrounded by 12 Gd³⁺ ions as second next neighbors leading to an electrostatic repulsion. Because of the twisting, four out of 12 Si–Gd distances become extensively larger resulting in 401.9(1) pm (4 × Si–Gd2) compared with 314.7(2) pm (4 × Si–Gd2) and 325.2(1) pm (4 × Si–Gd1), respectively. A similar effect has been observed in Ba₃MO ($M = \text{Ge, Si}$) (13). Additionally, the O–Gd2 distances (239.8(1) pm) are slightly shortened (O–Gd1: 269.8(2) pm) and thus the elongation of the OGd₆ octahedra is achieved and the distances fit better into the range of typical O–Gd distances (226.2–238.5 pm in Gd₂O₃ (26), sum of the ionic radii (Gd^{8l}): 240–246 pm (27)). The Gd³⁺ are coordinated ten- and eight-fold, respectively; the coordination spheres are shown in Fig. 4. The distances Gd1^{10l}–X ($X = \text{O, N}$) range between 269.8(2) and 273.9(7) pm, while in contrast the distances Gd2^{8l}–X ($X = \text{O, N}$) are distributed quite heterogeneously between 231(1) and 261.9(9) pm.

TABLE 2
Atomic Coordinates and Anisotropic Displacement Parameters for Gd₃[SiON₃]O (e.s.d's. in Parentheses)
for the Refinement at 293 K

Atom	Wyckoff symbol	f. o. f. ^a	x	y	z	U ₁₁	U ₂₂	U ₃₃	U ₂₃	U ₁₃	U ₁₂	U _{eq}
Gd(1)	4a	0	0	0	$\frac{1}{4}$	217(7)	217(7)	130(9)	0	0	0	188(6)
Gd(2)	8h	0.67611(9)	0.67611(9)	0.17611(9)	0	83(5)	83(5)	75(6)	0	0	-4(4)	81(5)
Si(1)	4b	0	0	$\frac{1}{2}$	$\frac{1}{4}$	90(26)	90(26)	77(41)	0	0	0	85(16)
N(1)	16l	0.75	0.141(2)	0.641(2)	0.1478(9)	352(40)	352(40)	146(51)	31(43)	31(43)	-132(72)	283(27)
O(1)	16l	0.25	0.141(2)	0.641(2)	0.1478(9)	352(40)	352(40)	146(51)	31(43)	31(43)	-132(72)	283(27)
O(2)	4c	0	0	0	0	173(77)	173(77)	1241(257)	0	0	0	529(81)

^af. o. f. = fractional occupancy factor.

Note. The anisotropic temperature factor is given as $\exp[-2\pi^2(U_{11}h^2a^{*2} + \dots + 2U_{13}hla^*c^*)]$. U_{eq} is defined as one-third of the trace of the U_{ij} tensor.

The exact symmetry reduction starting from perovskite down to Gd₃[SiON₃]O starts from space group $Pm\bar{3}m$ (no. 221) via a $k2$ transition to $Fm\bar{3}c$ (no. 226); an example for a similar phase crystallizing in the latter space group is Sr₂Fe₂O₅ (only $\frac{5}{6}$ of the O-position are occupied) (28). Subsequent $t3$ transition leads to the space group of the herein described gadolinium sion oxide, viz. $I4/mcm$. Further details relating to this discussion are presented in Table 7. In all the three discussed isotypic phases, the octahedra are elongated with a deviation from the average $X-M$ distance (in the respective XM_6 octahedron) of 2.2% in Ba₃[SiO₄]O (OBa₆), 2.4% in Cs₃[CoCl₄]Cl (ClCs₆), and 5.3% in Gd₃[SiON₃]O (OGd₆), respectively. As this elongation is the largest for Gd₃[SiON₃]O, it seemed possible that a crystallographic splitting of the central oxygen atom in the OGd₆ octahedron occurs at lower temperatures. Therefore, an investigation at $T=123$ K was carried out.

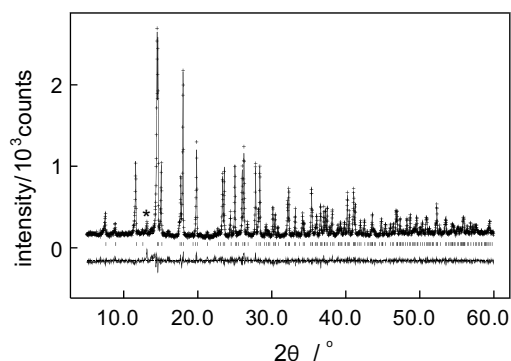


FIG. 1. Observed (crosses) and calculated (line) X-ray powder diffraction pattern (MoK α radiation) as well as the difference profile of the Rietveld refinement of Gd₃[SiON₃]O. The row of vertical lines indicates possible peak positions of Gd₃[SiON₃]O. The asterisk at $2\theta = 13.0^\circ$ represents the strongest reflection of the by-product Gd₂O₃.

Crystal Structure Analysis at $T=123$ K

X-ray diffraction data of the title compound Gd₃[SiON₃]O were collected on a Stoe Stadi4 four-circle diffractometer using MoK α radiation. Both at $T=123$ and $T=293$ K the same extinction conditions were observed.

The structure solution and refinement was again only possible in space group $I4/mcm$ (no. 140). The crystal structure of Gd₃[SiON₃]O was solved by direct methods using SHELXTL (19) and refined with anisotropic displacement parameters for all atoms. The relevant crystallographic data and further details of the X-ray data collection are summarized in Table 3. Table 4 shows the positional and displacement parameters for all atoms. In Table 5, selected interatomic distances and angles are listed.

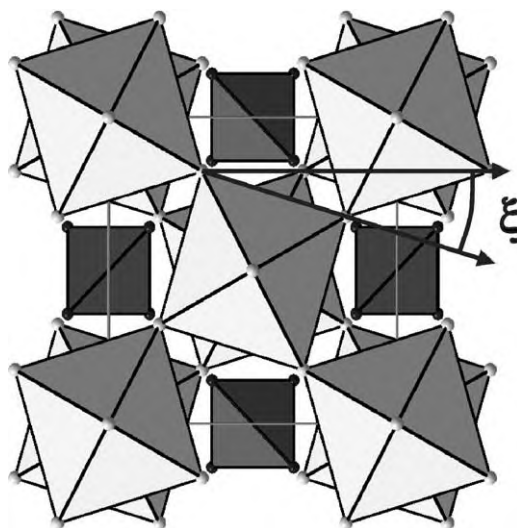


FIG. 2. Crystal structure of Gd₃[SiON₃]O viewed along [001]; the SiON₃ tetrahedra are shown as closed dark polyhedra and the OGd₆ octahedra are shown as closed bright polyhedra; the twisting angle ζ is indicated.

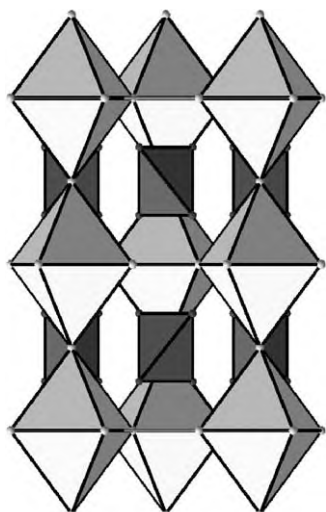


FIG. 3. Crystal structure of $Gd_3[SiON_3]O$ viewed along $[010]$; the $SiON_3$ tetrahedra are shown as closed dark polyhedra and the OGd_6 octahedra are shown as closed bright polyhedra.

The structure was also refined using space group $I4cm$ (no. 108) which requires the same extinction conditions as the chosen space group $I4/mcm$ (no. 140) to avoid the crystallographic splitting of atom O(2), but this did not lead to better R values and satisfactory results. Also the refined Flack parameter could not be determined reliably and it was impossible to determine reasonable anisotropic displacement parameters for all atoms.

Because of the statistical assignment of O/3N to the anionic position of the SiX_4 tetrahedron, it seemed possible that there might be a superstructure with an ordered distribution of $SiON_3$ tetrahedra. Furthermore, the absence of body centering of several M_3BX_5 phases has been intensively discussed in the past (see Refs. (8, 9, 25); hence, we focussed carefully on these points. The unit cell and the

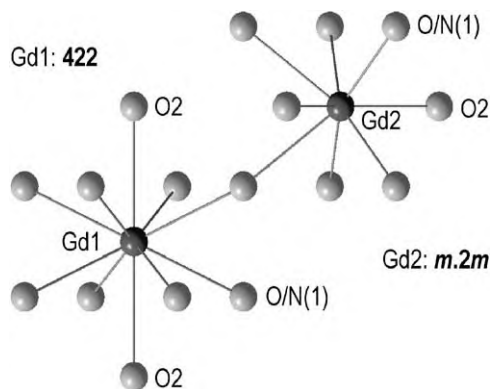


FIG. 4. Coordination of the Gd atoms in $Gd_3[SiON_3]O$ at 293 K; the respective site symmetries are indicated.

TABLE 3
Crystallographic Data of $Gd_3[SiON_3]O$ (e.s.d's. in Parentheses)
for the Refinement at 123 K

<i>Crystal data</i>	
$Gd_3[SiON_3]O$	$F(000) = 972$
$M = 573.87$ g/mol	$\rho = 8.387$ g/cm
Tetragonal	MoK α -radiation
Space group $I4/mcm$ (no. 140)	$\lambda = 71.073$ pm
$a = 649.1(2)$ pm	$\mu = 43.25$ mm $^{-1}$
$c = 1078.8(6)$ pm	$T = 123(2)$ K
$V = 454.5(3) \times 10^6$ pm 3	Block
	$0.211 \times 0.149 \times 0.080$ mm 3
$Z = 4$	Yellow
<i>Data collection (123 K)</i>	
Stoe STADI4	Measured octants: all
Absorption correction:	$h = -11 \rightarrow 11$
numerical (ψ -scans)	$k = -11 \rightarrow 11$
$T_{min} = 0.0317$; $T_{max} = 0.0769$	$l = -19 \rightarrow 19$
$R_{int} = 0.1275$	405 independent reflections
$2\theta_{max} = 79.9^\circ$	360 observed reflections ($F_o^2 \geq 4\sigma(F_o^2)$)
<i>Refinement (123 K)</i>	
Refinement on F^2	Program used to refine structure:
$R_1 = 0.0411$ (all data)	SHELXL-97 (19)
$wR_2 = 0.0769$ (all data)	$w^{-1} = \sigma^2 F_o^2 + (xP)^2 + yP$;
	$P = (F_o^2 + 2F_c^2)/3$
	Weighting scheme (x/y) 0.0202/
	20.1403
Goof = 1.250	Extinction coefficient: 0.0157(9)
13019 measured reflections	Min. residual electron density:
	-2.78 e \AA^{-3}
19 parameters	Max. residual electron density:
	2.62 e \AA^{-3}

extinction conditions were confirmed by a complete set of precession photographs. Reflections indicating a superstructure have not been detected.

At $T = 123$ K, a crystallographic splitting of O(2) was found. The resulting distances O(2)–Gd are almost equal and the coordination environment of O(2) can be described as a square pyramid. The angle Gd(1)–O(2)–Gd(2) is slightly increased from 90° (293 K) to $96.7(5)^\circ$. At room temperature, this crystallographic splitting could not be resolved and accordingly elongated OGd_6 octahedra are observed (Fig. 5).

OPTICAL PROPERTIES

UV-Vis Spectroscopy

The energy level scheme of Gd^{3+} is well known (29) and as Gd^{3+} being isoelectronic with Eu^{2+} similar UV-Vis spectra showing very broad bands are observed. But in contrast to Eu^{2+} where the transition between its ground state $4f^7$ and the excited state $4f^6 5d^1$ is normally observed in the visible region, Gd^{3+} -containing

TABLE 4
Atomic Coordinates and Anisotropic Displacement Parameters for Gd₃[SiON₃]O (e.s.d.'s. in Parentheses)
for the Refinement at 123 K

Atom	Wyckoff symbol	f. o. f. ^a	x	y	z	U ₁₁	U ₂₂	U ₃₃	U ₂₃	U ₁₃	U ₁₂	U _{eq}
Gd(1)	4a		0	0	$\frac{1}{4}$	187(3)	187(3)	120(4)	0	0	0	165(3)
Gd(2)	8h		0.67590(6)	0.17590(6)	0	75(2)	75(2)	74(3)	0	0	-1(2)	75(2)
Si(1)	4b		0	$\frac{1}{2}$	$\frac{1}{4}$	90(11)	90(11)	68(15)	0	0	0	83(7)
N(1)	16l	0.75	0.142(2)	0.642(2)	0.1479(8)	318(31)	318(31)	113(26)	25(20)	25(20)	-193(41)	250(20)
O(1)	16l	0.25	0.142(2)	0.642(2)	0.1479(8)	318(31)	318(31)	113(26)	25(20)	25(20)	-193(41)	250(20)
O(2)	8f	0.5	0	0	0.026(2)	156(44)	156(44)	185(93)	0	0	0	166(34)

^af. o. f. = fractional occupancy factor.

Note. The anisotropic temperature factor is given as $\exp[-2\pi^2(U_{11}h^2a^{*2} + \dots + 2U_{13}hla^*c^*)]$. U_{eq} is defined as one-third of the trace of the U_{ij} tensor.

compounds are usually colorless. In Contrast to the 4f-states, the 5d-states are strongly influenced by the coordination sphere in the host lattice; due to the nephelauxetic effect (N^{3-}/O^{2-}) the ligand field splitting of the 5d-levels is expected to become larger and in consequence the observed transitions are red shifted. This

has been convincingly shown for Ce³⁺-doped Y-Si-O-N compounds (30) or Eu²⁺-doped Ba₂[Si₅N₈] (31). And this also holds for Gd₃[SiON₃]O which has a yellowish color. Thus, the optical reflectance spectra were measured (Fig. 6). These revealed two overlaying broad bands, one peaking at almost the same wavelength as observed in gadolinium oxide (340 nm) and a second red-shifted band at approximately 400 nm.

TABLE 5
Selected Interatomic Distances (pm) and Angles (deg) for Gd₃[SiON₃]O at 293 and 123 K, Respectively (e.s.d.'s. in Parentheses)

		Measurement at 293 K	Measurement at 123 K
Gd(1)	-O(2) ^[0] (2 ×)	269.8(2)	241(2), 298(2)
	-O(1) ^[1] /N(1) ^[1] (8 ×)	273.9(7)	273.0(6)
Gd(2)	-O(1) ^[1] /N(1) ^[1] (2 ×)	231(1)	230.6(9)
	-O(2) ^[0] (2 ×)	239.8(1)	241.0(3)
	-O(1) ^[1] /N(1) ^[1] (4 ×)	261.9(9)	262.0(8)
	-Gd(2)		322.9(1)
	-Gd(1)		360.6(1)
Si(1)	-O(1) ^[1] /N(1) ^[1] (4 ×)	171(1)	171.1(9)
O(1)/N(1)	-Si(1) ^[4]	171(1)	171.1(9)
	-Gd(2) ^[8]	231(1)	230.6(9)
	-Gd(2) ^[8] (2 ×)	261.9(9)	262.0(8)
	-Gd(1) ^[10] (2 ×)	273.9(7)	273.0(6)
O(2)	-O(2) ^[0]	—	56(4)
	-Gd(2) ^[8] (4 ×)	239.8(1)	241.0(3)
	-Gd(1) ^[10]	269.8(2)	241(2)
	-Gd(1) ^[10]	269.8(2)	298(2)
O ^[1] /N ^[1] —Si—O ^[1] /N ^[1]		99.3(4)–114.7(4)	99.8(6)–114.5(4)

Vibrational Spectroscopy

Normally, the vibrations of SiO₄ tetrahedra in orthosilicates range between 1000 and 400 cm⁻¹ as observed in olivine (32) or zirconite (33). Valence vibrations are found above 860 cm⁻¹, and deformation modes below 620 cm⁻¹. The Si-N bond is expected to be weaker than the Si-O bond. Thus, the vibrations of the SiON₃ tetrahedra in Gd₃[SiON₃]O occur at lower wavenumbers (Fig. 7). Unfortunately, very broad unresolved bands at 885 and

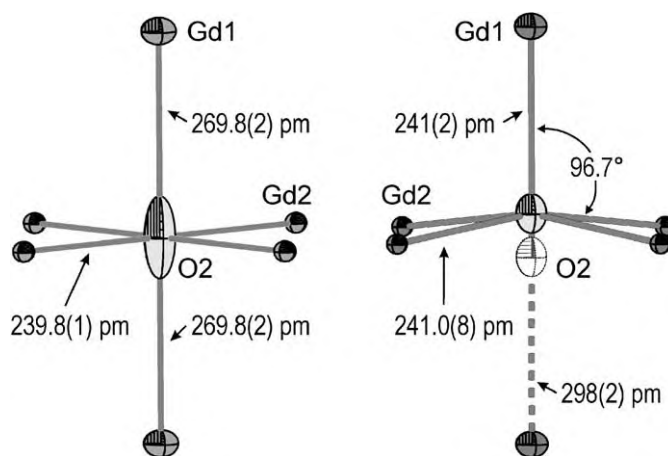


FIG. 5. Coordination of the O2 atom in Gd₃[SiON₃]O at 293 K (left) and 123 K (right, both positions of the crystallographically splitted O2 atom are presented).

TABLE 6
Results of the MAPLE Calculations for Gd₃[SiON₃]O and Increment Calculations in kJ/mol at 293 and 123 K, Respectively

	Measurement at 293 K	Measurement at 123 K
Gd(1)	4350	4462
Gd(2)	4287	4150
Si(1)	9838	9988
O(1)/N(1)	4124	4103
O(2)	1993	1967

Typical partial MAPLE values (in kJ/mol)^a

MAPLE(3GdN + SiO ₂)	MAPLE(Gd ₃ [SiON ₃]O) (293 K)		MAPLE(Gd ₃ [SiON ₃]O) (123 K)	
41 598	41 721	$\Delta^b = 0.3\%$	41440	$\Delta = 0.4\%$

^aGd³⁺: 3900–4550; Si⁴⁺: 9000–10 200; N³⁻: 5000–6000; O²⁻: 2000–2800; (O_{1/4}N_{3/4})^{-2.75}: 4000–5200.

^b Δ = difference.

693 cm⁻¹, respectively, are observed and thus a precise assignment is impossible. In the olivine spectra two very strong broad bands have been observed at 1005 and 882 cm⁻¹, respectively. Below 600 cm⁻¹, the additional vibrations of the OGD₆ units have to be considered and the IR spectrum, becomes very complex. In the Raman spectrum, we observe broad weak bands around 875 and 740 cm⁻¹, and two quite sharp bands peaking at 583 and 533 cm⁻¹, respectively. In olivine, similar bands have been found at 960, 917, 854 and 822 cm⁻¹, respectively.

MAGNETIC PROPERTIES

The temperature dependence of the inverse magnetic susceptibility (0.5 T data) of Gd₃[SiON₃]O is displayed in Fig. 8. Over the whole temperature range we observe Curie–Weiss behavior $\chi = C/(T - \Theta)$ with an experimental magnetic moment of 7.68(5) μ_B /Gd, close to the free ion value of 7.94 μ_B /Gd³⁺ (see Ref. (34)). The paramagnetic Curie temperature (Weiss constant) of $\Theta = -7(1)$ K was determined by linear extrapolation of the 1/ χ vs T data to

1/ $\chi = 0$. According to the small Weiss constant, we expect weak antiferromagnetic interactions of the gadolinium magnetic moments at very low temperatures. As presented in Fig. 9, the low-field (0.002 T) zero-field cooling (zfc) and field cooling (fc) measurements gave no indication for magnetic ordering down to 2 K.

CONCLUSIONS

Gd₃[SiON₃]O is one of the rare oxonitridosilicates with a non-condensed Si/O/N substructure. Other examples are Li₆[SiN₂O₂] (35), the silicoapatites Ln₁₀[SiO_{3.67}N_{0.33}]₆O₂ (Ln = La, Nd, Sm, Gd) and M₁₀[SiO₂N₂]₆O₂ (M = Ti, Ge) (36). The nitrogen atoms are located completely in the SiX₄ tetrahedra. Another example crystallizing isotypic with β -K₂SO₄ are the sions LnEu[SiO₃N] (Ln = La, Nd, Sm) (37). Typically, the materials properties of oxonitridosilicates like inertness against hydrolysis, thermal stability, and mechanical hardness are strongly influenced by the degree of condensation of the Si/O/N substructures. Accordingly, Gd₃[SiON₃]O unlike the higher condensed

TABLE 7
Relevant Data of Perovskite, Gd₃[SiON₃]O and Several Isotypic A₃BX₅ Phases (e.s.d's. in Parentheses)

Compound	a/c ratio	Angle ξ (deg)	Deviation of the resp. XM ₆ octahedron
Gd ₃ [SiON ₃]O (293 K)	0.603(1)	16.47(1)	5.3% ($X = O$, $M = Gd$)
Gd ₃ [SiON ₃]O (123 K)	0.602(1)	16.51(1)	no octahedron
Ba ₃ [SiO ₄]O	0.651	14.96	2.2% ($X = O$, $M = Ba$)
Cs ₃ [CoCl ₄]Cl	0.635	19.34	2.4% ($X = Cl$, $M = Cs$)
Ca[TiO ₃] (in a body-centered tetragonal cell setting)	$\sqrt{2}/2 \approx 0.7$	0	None ($X = Ti$, $M = O$)

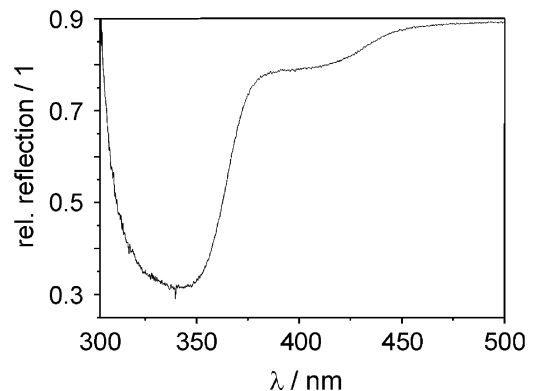


FIG. 6. UV–Vis absorption spectrum of Gd₃[SiON₃]O at 293 K.

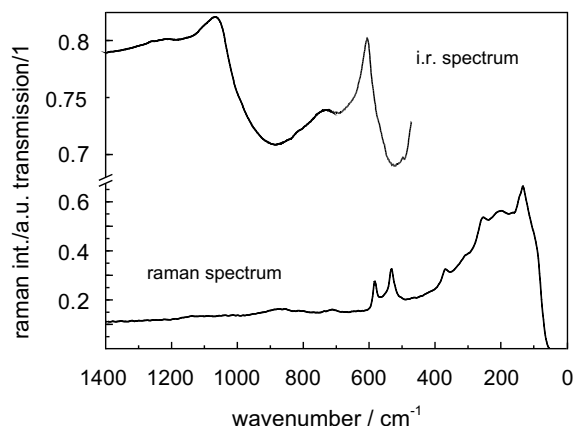


FIG. 7. Infrared vibrational spectrum (top) and Raman spectrum (bottom) of $Gd_3[SiON_3]O$ recorded at room temperature.

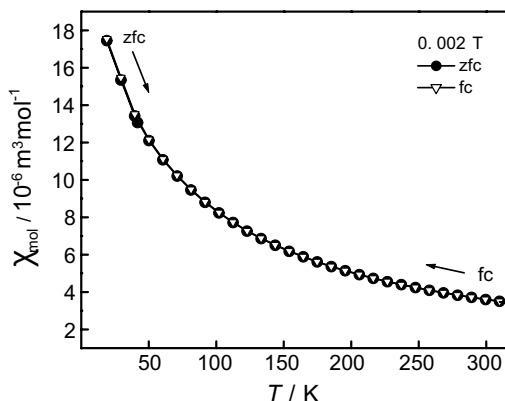


FIG. 9. Low-temperature susceptibility of $Gd_3[SiON_3]O$ measured at an external flux density of 0.002 T in the zfc (black circles) and fc (white triangles) modus.

nitridosilicates and oxonitridosilicates undergoes slow hydrolysis in humid air.

Interestingly, most oxonitridosilicates obtained so far exhibit a rather high degree of condensation of their Si/O/N substructures, and thus they show a high chemical stability against hydrolysis (3). Presumably, the highly condensed network structures are a direct consequence of the severe high-temperature conditions during the synthesis of these compounds in the radiofrequency furnaces. Apparently, only the most stable structures survive these reaction conditions. Due to lattice energetic reasons, the perovskite structure type is fairly stable as well and thus $Gd_3[SiON_3]O$ representing the anti-type is obtained under similar conditions in the radiofrequency furnace. Recently $Ce_{16}[Si_{15}O_6N_{32}]$, another oxonitridosilicate, was described, which represents a superstructure of a defect variant of the

perovskite structure type, where most of the octahedra have been substituted by tetrahedra (38).

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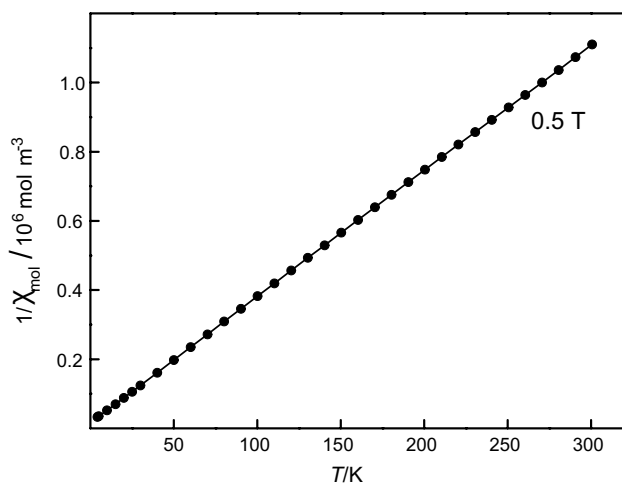


FIG. 8. Temperature dependence of the inverse magnetic susceptibility of $Gd_3[SiON_3]O$ measured at a flux density of 0.5 T.

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